L Number	Hits	Search Text	DB	Time stamp
58	4	gunn and pinguet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:37
59	2	gunn and pinguet and germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:37
60	6	luxtera	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:38
61	2	luxtera and germanium	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:39
62	0	(waveguide same (core with germanium with silicon with heterojunction))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:40
63	0	((core with germanium with silicon with heterojunction))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:41
64	0	((core with germanium with heterojunction))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:41
65	2243	((core with germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:42
66	219	waveguide same cladding with ((core with germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:42
67	295	waveguide same cladding same ((core with germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:42

68	0	waveguide same cladding same ((core with germanium)) same heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:42
69	63	waveguide same cladding same ((core with germanium) with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:43
70	0	waveguide same (cladding with (insulating or dielectric)) same ((core with germanium) with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:43
71	63	waveguide same (cladding) same ((core with germanium) with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:44
72	0	waveguide same (cladding) same ((core with germanium) with silicon) same (dielectric or insulating)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:44
73	63	waveguide same (cladding) same ((core with germanium) with silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:45
74	46	waveguide same (cladding) same ((core near10 germanium near10 silicon))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:45
75	4	(waveguide same (cladding) same ((core near10 germanium near10 silicon))).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:47
76	13176	heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:47
77	117	silicon adj heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:47

78	0	silicon adj heterojunction and luxtera	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:47
79	3	silicon adj heterojunction and gunn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:47
88	468	waveguide and core and cladding and (heterostructure or heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:49
89	0	waveguide and core and cladding and (heterostructure or heterojunction) and gunn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:49
90	63	(US-6699765-$ or US-6690871-$ or US-6690844-$ or US-6671443-$ or US-6654511-$ or US-6646747-$ or US-6640021-$ or US-6625348-$ or US-6611636-$ or US-6608945-$ or US-6554491-$ or US-6556735-$ or US-6442977-$ or US-6449420-$ or US-6396988-$ or US-6441906-$ or US-6316281-$ or US-6389209-$ or US-6391214-$ or US-6337937-$ or US-6355886-$ or US-6192712-$ or US-6222951-$ or US-6075908-$ or US-5915051-$ or US-5917981-$).did. or (US-5841930-$ or US-5790726-$ or US-5793913-$ or US-5708739-$ or US-5625729-$ or US-5682455-$ or US-5495548-$ or US-5280189-$ or US-5132811-$ or US-5347601-$ or US-4747663-$ or US-4997246-$ or US-3843229-$ or US-6788847-$ or US-6768856-$).did. or (US-20040005131-$ or US-20030235933-$ or US-20030231851-$ or US-20030179981-$ or US-20030176075-$ or US-20030161571-$ or US-20030100824-$ or US-20030003735-$ or US-20020164137-$ or US-20020154878-$ or US-20020106174-$ or US-20020021879-$ or US-20040156590-$ or US-20040156589-$ or US-20040092104-$ or US-20040008968-$).did. or (EP-793121-$).did. or (JP-09318830-$).did. or (EP-1343199-$ or EP-793121-$ or US-20040092104-$ or WO-200282134-$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/15 13:49

91	12	((US-6699765-$ or US-6690871-$ or US-6690844-$ or US-6671443-$ or US-6654511-$ or US-6646747-$ or US-6640021-$ or US-6625348-$ or US-6611636-$ or US-6608945-$ or US-6554491-$ or US-6556735-$ or US-6442977-$ or US-6449420-$ or US-6396988-$ or US-6441906-$ or US-6316281-$ or US-6389209-$ or US-6391214-$ or US-6337937-$ or US-6355886-$ or US-6192712-$ or US-6222951-$ or US-6075908-$ or US-5915051-$ or US-5917981-$).did. or (US-5841930-$ or US-5790726-$ or US-5793913-$ or US-5708739-$ or US-5625729-$ or US-5682455-$ or US-5495548-$ or US-5280189-$ or US-5132811-$ or US-5347601-$ or US-4747663-$ or US-4997246-$ or US-3843229-$ or US-6788847-$ or US-6768856-$).did. or (US-20040005131-$ or US-20030235933-$ or US-20030231851-$ or US-20030179981-$ or US-20030176075-$ or US-20030161571-$ or US-20030100824-$ or US-20030003735-$ or US-20020164137-$ or US-20020154878-$ or US-20020106174-$ or US-20020021879-$ or US-20040156590-$ or US-20040156589-$ or US-20040092104-$ or US-20040008968-$).did. or (EP-793121-$).did. or (JP-09318830-$).did. or (EP-1343199-$ or EP-793121-$ or US-20040092104-$ or WO-200282134-$).did.) and (heterostructure or heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:50
92	0	"10600563" and (heterostructure or heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:50
93	0	"10/600563" and (heterostructure or heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:51
94	0	"10/600563"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:50

95	20576	heterostructure or heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:51
96	637	(heterostructure or heterojunction) near10 ((si/ge) or (silicon/germanium) or germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:52
97	1	(heterostructure or heterojunction) near10 ((si/ge) or (silicon/germanium) or germanium) and luxtera	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:52
98	4	(heterostructure or heterojunction) near10 ((si/ge) or (silicon/germanium) or germanium) and (gunn or luxtera)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:53
99	0	((heterostructure or heterojunction) near10 ((si/ge) or (silicon/germanium) or germanium)) same waveguide same cladding same core same (insulating or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:56
100	1	(core with (heterostructure or heterojunction) near10 ((si/ge) or (silicon/germanium) or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:56
101	4	(core with (heterostructure or heterojunction or hetero-structure or hetero-junction) with ((si/ge) or (silicon/germanium) or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:01
102	652	((heterojunction or hetero-junction) with ((si/ge) or (silicon/germanium) or germanium))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:01
103	0	((heterojunction or hetero-junction) with ((si/ge) or (silicon/germanium) or germanium)) same core	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:02
104	1	((heterojunction or hetero-junction) with ((si/ge) or (silicon/germanium) or germanium)) same (waveguide or core or cladding)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:03

105	0	core near10 (silicon adj layer) near10 (germanium adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:04
106	0	core with (silicon adj layer) near10 (germanium adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:04
107	0	core with (silicon adj layer) with (germanium adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:04
108	3	core with (silicon) with (germanium adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:04
109	295	core with (silicon) with (germanium)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:04
110	131	(core with (silicon) with (germanium)) same cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:05
111	63	(core with (silicon) with (germanium)) same cladding same waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:05
112	5	((core with (silicon) with (germanium)) same cladding same waveguide).clm.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:06
113	11	(silicon adj layer) and (germanium adj layer) and cladding and core and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:11
114	0	germanium adj on adj silicon adj heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:12

115	160	germanium near silicon near heterojunction	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:12
116	0	core with (germanium near silicon near heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:12
117	0	core with ((ge or germanium) near (si or silicon) near heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:13
118	0	core with ((ge or germanium) near5 (si or silicon) near5 heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:13
119	0	core same ((ge or germanium) near5 (si or silicon) near5 heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:13
120	437	((ge or germanium) near5 (si or silicon) near5 heterojunction)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:13
121	1	((ge or germanium) near5 (si or silicon) near5 heterojunction) and core and cladding and waveguide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:14
122	0	(core with ((silicon or si) adj layer)) with ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:15
123	0	core with ((silicon or si) adj layer) with ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:15
124	1	core same ((silicon or si) adj layer) with ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:16

125	6	core and cladding and ((silicon or si) adj layer) with ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:18
126	6	luxtera	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:19
127	3	luxtera and (germanium or ge)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:20
128	1014	(germanium adj layer) not near2 silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:21
129	3255	((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:21
130	1572	((germanium or ge) adj layer) near (silicon or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:21
131	1683	(((germanium or ge) adj layer)) not (((germanium or ge) adj layer) near (silicon or si))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:22
132	148	((((germanium or ge) adj layer)) not (((germanium or ge) adj layer) near (silicon or si))) and (photodetector or waveguide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:22
133	41	((((germanium or ge) adj layer)) not (((germanium or ge) adj layer) near (silicon or si))) and (photodetector or waveguide) and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:22
134	23	((((germanium or ge) adj layer)) not (((germanium or ge) adj layer) near (silicon or si))) and (photodetector or waveguide) and cladding and core	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:41

135	1424	((silicon or si) adj layer) and ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:43
136	1311	(((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near2 (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47
137	113	(((silicon or si) adj layer) and ((germanium or ge) adj layer)) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near2 (germanium or ge)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47

138	5	((((silicon or si) adj layer) and ((germanium or ge) adj layer)) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near2 (germanium or ge)))) and (photodetector or waveguide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:45
139	5	((((silicon or si) adj layer) and ((germanium or ge) adj layer)) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near2 (germanium or ge)))) and (photodetector or waveguide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47

140	3	((((silicon or si) adj layer) and ((germanium or ge) adj layer)) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near2 (germanium or ge))) and (photodetector or waveguide) and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47
141	1240	(((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near (germanium or ge))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:47
142	184	(((silicon or si) adj layer) and ((germanium or ge) adj layer)) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near (germanium or ge)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:48

143	4	((((silicon or si) adj layer) and ((germanium or ge) adj layer)) not ((((silicon or si) adj layer) and ((germanium or ge) adj layer)) and ((silicon or si) near (germanium or ge))) and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:48
144	1424	((silicon or si) adj layer) and ((germanium or ge) adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:49
145	33	((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:49
146	18	((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:49
147	15	((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core and (waveguide or photodetector)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:26
148	6	(((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core and (waveguide or photodetector)) and (silicon near5 (contact or conducting or conductive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:27
149	6	(((silicon or si) adj layer) and ((germanium or ge) adj layer) and cladding and core and (waveguide or photodetector)) and (silicon near10 (contact or conducting or conductive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:28

150	85	(US-6699765-$ or US-6690871-$ or US-6690844-$ or US-6671443-$ or US-6654511-$ or US-6646747-$ or US-6640021-$ or US-6625348-$ or US-6611636-$ or US-6608945-$ or US-6554491-$ or US-6556735-$ or US-6442977-$ or US-6449420-$ or US-6396988-$ or US-6441906-$ or US-6316281-$ or US-6389209-$ or US-6391214-$ or US-6337937-$ or US-6355886-$ or US-6192712-$ or US-6222951-$ or US-6075908-$ or US-5915051-$ or US-5917981-$).did. or (US-5841930-$ or US-5790726-$ or US-5793913-$ or US-5708739-$ or US-5625729-$ or US-5682455-$ or US-5495548-$ or US-5280189-$ or US-5132811-$ or US-5347601-$ or US-4747663-$ or US-4997246-$ or US-3843229-$ or US-6788847-$ or US-6768856-$ or US-6158901-$ or US-6734453-$ or US-6684007-$ or US-5533156-$ or US-5465312-$ or US-6075253-$ or US-6472594-$ or US-5861324-$ or US-5681402-$ or US-6463088-$ or US-4717225-$ or US-4715875-$).did. or (US-4711525-$ or US-4597787-$ or US-4426129-$ or US-4261771-$ or US-4205329-$).did. or (US-20040005131-$ or US-20030235933-$ or US-20030231851-$ or US-20030179981-$ or US-20030176075-$ or US-20030161571-$ or US-20030100824-$ or US-20030003735-$ or US-20020164137-$ or US-20020154878-$ or US-20020106174-$ or US-20020021879-$ or US-20040156590-$ or US-20040156589-$ or US-20040092104-$ or US-20040008968-$ or US-20040056243-$ or US-20020048289-$ or US-20020028045-$).did. or (EP-793121-$).did. or (JP-09318830-$ or JP-59141276-$).did. or (EP-1343199-$ or EP-793121-$ or US-20040092104-$ or WO-200282134-$ or US-20030102469-$).did.	USPAT; US-PGPUB; EPO; JPO; DERWENT	2004/09/15 15:28

151	24	((US-6699765-$ or US-6690871-$ or US-6690844-$ or US-6671443-$ or US-6654511-$ or US-6646747-$ or US-6640021-$ or US-6625348-$ or US-6611636-$ or US-6608945-$ or US-6554491-$ or US-6556735-$ or US-6442977-$ or US-6449420-$ or US-6396988-$ or US-6441906-$ or US-6316281-$ or US-6389209-$ or US-6391214-$ or US-6337937-$ or US-6355886-$ or US-6192712-$ or US-6222951-$ or US-6075908-$ or US-5915051-$ or US-5917981-$).did. or (US-5841930-$ or US-5790726-$ or US-5793913-$ or US-5708739-$ or US-5625729-$ or US-5682455-$ or US-5495548-$ or US-5280189-$ or US-5132811-$ or US-5347601-$ or US-4747663-$ or US-4997246-$ or US-3843229-$ or US-6788847-$ or US-6768856-$ or US-6158901-$ or US-6734453-$ or US-6684007-$ or US-5533156-$ or US-5465312-$ or US-6075253-$ or US-6472594-$ or US-5861324-$ or US-5681402-$ or US-6463088-$ or US-4717225-$ or US-4715875-$).did. or (US-4711525-$ or US-4597787-$ or US-4426129-$ or US-4261771-$ or US-4205329-$).did. or (US-20040005131-$ or US-20030235933-$ or US-20030231851-$ or US-20030179981-$ or US-20030176075-$ or US-20030161571-$ or US-20030100824-$ or US-20030003735-$ or US-20020164137-$ or US-20020154878-$ or US-20020106174-$ or US-20020021879-$ or US-20040156590-$ or US-20040156589-$ or US-20040092104-$ or US-20040008968-$ or US-20040056243-$ or US-20020048289-$ or US-20020028045-$).did. or (EP-793121-$).did. or (JP-09318830-$ or JP-59141276-$).did. or (EP-1343199-$ or EP-793121-$ or US-20040092104-$ or WO-200282134-$ or US-20030102469-$).did.) and (silicon near10 (contact or conducting or conductive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:29

152	2	((US-6699765-$ or US-6690871-$ or US-6690844-$ or US-6671443-$ or US-6654511-$ or US-6646747-$ or US-6640021-$ or US-6625348-$ or US-6611636-$ or US-6608945-$ or US-6554491-$ or US-6556735-$ or US-6442977-$ or US-6449420-$ or US-6396988-$ or US-6441906-$ or US-6316281-$ or US-6389209-$ or US-6391214-$ or US-6337937-$ or US-6355886-$ or US-6192712-$ or US-6222951-$ or US-6075908-$ or US-5915051-$ or US-5917981-$).did. or (US-5841930-$ or US-5790726-$ or US-5793913-$ or US-5708739-$ or US-5625729-$ or US-5682455-$ or US-5495548-$ or US-5280189-$ or US-5132811-$ or US-5347601-$ or US-4747663-$ or US-4997246-$ or US-3843229-$ or US-6788847-$ or US-6768856-$ or US-6158901-$ or US-6734453-$ or US-6684007-$ or US-5533156-$ or US-5465312-$ or US-6075253-$ or US-6472594-$ or US-5861324-$ or US-5681402-$ or US-6463088-$ or US-4717225-$ or US-4715875-$).did. or (US-4711525-$ or US-4597787-$ or US-4426129-$ or US-4261771-$ or US-4205329-$).did. or (US-20040005131-$ or US-20030235933-$ or US-20030231851-$ or US-20030179981-$ or US-20030176075-$ or US-20030161571-$ or US-20030100824-$ or US-20030003735-$ or US-20020164137-$ or US-20020154878-$ or US-20020106174-$ or US-20020021879-$ or US-20040156590-$ or US-20040156589-$ or US-20040092104-$ or US-20040008968-$ or US-20040056243-$ or US-20020048289-$ or US-20020028045-$).did. or (EP-793121-$).did. or (JP-09318830-$ or JP-59141276-$).did. or (EP-1343199-$ or EP-793121-$ or US-20040092104-$ or WO-200282134-$ or US-20030102469-$).did.) and (((si or silicon) adj layer) near10 (contact or conducting or conductive))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 15:29